MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED



Product specification





Features

- 100W peak pulse power (t_P = 8/20µs)
- DFN2510-10 Package
- Working voltage: 5.0V
- Low clamping voltage
- Low capacitance
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) ±30KV(air), ±15KV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)
 IEC 61000-4-5 (Lightning) 5A (8/20us)

Mechanical Characteristics

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- MSD Level: MSL-1
- Qualified max reflow temperature:260°C
- Pure tin plating: 7 ~ 17 um
- Pin flatness:≤3mil

Applications

- USB 2.0,3.0 Power & Data Line Protection
- DVI & HDMI Port Protection
- Serial ATA Port Protection
- Mobile Handsets
- Digital Cameras and camcorders
- PDA & MP3 Players
- Digital TV and Set-top Boxes
- Other Portable Electronic Components

Order information

PACKAGE OUTLINE	Circuit Diagram	Marking		
	NC NC GND NC NC 10 9 8 7 6 10 9 4 7 6 10 9 10 10 10 10 10 10 10 10 10 10 10 10 10	.05V4		
DFN2510-10				

Electronics Parameter

SKSEM

Symbol	Parameter		
Vrwm	Peak Reverse Working Voltage		
lR	Reverse Leakage Current @ VRWM		
VBR	Breakdown Voltage @ I⊤		
Г	Test Current		
IPP	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ IPP		
Ppp	Peak Pulse Power		
С	Junction Capacitance		
lF	Forward Current		
VF	Forward Voltage @ I⊧		



Electrical characteristics per line@(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	Vrwm				5	V
Breakdown Voltage	Vbr	k = 1mA	6			V
Reverse Leakage Current	R	V _{RWM} =5.0V, T=25℃			1	μA
Clamping Voltage	Vc	IPP = 1A, tP = 8/20µs			11	V
Clamping Voltage	Vc	I _{PP} =5A, t _P = 8/20μs			15	V
Junction Capacitance(IO-IO)	CJ	VR=0V, f = 1MHz		0.3	0.4	pF
Junction Capacitance(IO-GND)	CJ	V _R =0V, f = 1MHz		0.6	0.75	pF

Absolute maximum rating@ 25℃

Rating	Symbol	Value	Units
Peak Pulse Power (t _P =8/20µs)	P _{pp}	100	W
Operating Temperature	TJ	-55 to +150	°C
Storage Temperature	Тѕтс	-55 to +150	°C



TypicalCharacteristics



Fig 5.Non Repetitive Peak Pulse Power vs. Pulse time

Fig 6. TLP Measurement



SolderReflowRecommendation



Remark: Pb free for 260°C; Pb for 245°C.



Dimension (DFN2510-10)



Dimensions in Millimeter							
Symbol	Min.	Nom.	Max.	Symbol	Min.	Nom.	Max.
A	0.500	0.550	0.600	D	2.450	2.500	2.550
A1	0.00	/	0.05	E	0.950	1.00	1.050
A2	0.122	0.152	0.200	е	0.450	0.500	0.550
b	0.150	0.200	0.250	h	0.080	0.120	0.150
b1	0.200	0.250	0.300	k	0.150	0.200	0.250
b2	0.350	0.400	0.450	L	0.350	0.400	0.450
L1	0.075 REF		L2	0.05 REF			
φ	0.150	0.200	0.250				

REEL SPECIFICATION

P/N	PKG	QTY
ESD5304D-MS	DFN2510-10	3000



ESD5304D-MS

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